General and Inorganic Chemistry

Chemisorption of SO₂ and Cl₂ on indium oxide

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The mutual influence of SO_2 and Cl_2 during their consecutive chemisorption on the In_2O_3 surface has been investigated. It was found that SO_2 is chemisorbed in the uncharged form, and the amount of chemisorption decreases as the temperature increases. The preliminary chemisorption of Cl_2 results in a dramatic decrease in the amount of SO_2 sorbed and in a change in the character of the bonding of SO_2 with the oxide surface. When SO_2 is sorbed first, the temperature of the formation of chlorides during subsequent chemisorption of Cl_2 decreases.

Key words: chemisorption, surface, active sites, electric conductivity.

The studies on the chemisorption of SO_2 and Cl_2 on ZnO carried out previously showed that the character of the interaction of these gases with the surface of semiconducting oxides depends on the order in which they are adsorbed. In the present work we have studied the mutual influence of SO_2 and Cl_2 during their consecutive sorption on the surface of In_2O_3 .

Experimental

Investigations were carried out at 23-225 °C, the pressure of the gas being sorbed was 0.1-0.5 Torr, and the unit that was used allowed the variation of the pressure and of the electrical conductivity of the sample to be simultaneously recorded. The electrical conductivity varied in the range $10^{-7}-10^3$ Ohm cm⁻¹.

An $\rm In_2O_3$ specimen of the "pure" grade with $S_{\rm spec}$ = 6.0 m² g⁻¹ was used. Its electrical conductivity in air was 0.1 Ohm cm⁻¹. Prior to the experiment, the sample was

placed into a measuring cell and aged for 16-20 h at 350 °C until constant electrical conductivity (1.0-5.0 Ohm cm⁻¹) was attained, then the cell was filled with the gas to be sorbed. When the chemisorption was completed, the amount of reversibly sorbed gas was determined by freezing it out in a trap cooled with liquid nitrogen. Chemisorption was regarded as irreversible if no desorption from the surface occurred at the experimental temperature in the course of 2 h.

After the study of the interference of SO₂ and Cl₂ under the conditions of their consecutive chemisorption, the sample was evacuated for 2 h at the experimental temperature, and the second gas was introduced.

The composition of the products of the interaction was determined by the thermodesorption method using an MI-1201 mass spectrometer.²

Results and Discussion

The sorption of Cl₂ on the In₂O₃ surface (see Ref. 3) occurs irreversibly, increases with increasing tempera-

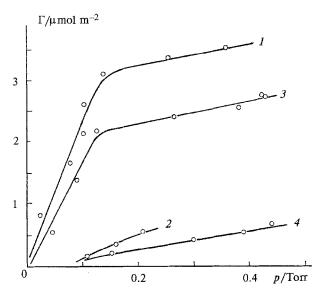


Fig. 1. Isotherms of the chemisorption of SO_2 on In_2O_3 at 23 °C (1, 2) and 200 °C (3, 4); 1, 3 are the irreversible form and 2, 4 are the reversible form.

ture, and is accompanied by a decrease in the electrical conductivity of the oxide due to localization of the conduction electrons on the sorbed particles.

The chemisorption of SO₂ occurs at a high rate; the kinetics of the chemisorption is described by the Zel'dovich—Roginskii equation:⁴

$$\Gamma = a \log \tau + b$$

Two forms of the adsorption of SO_2 were found in the temperature range studied, *i.e.*, reversible and irreversible adsorption. 90 % of the gas is sorbed reversibly. Figure 1 shows the isotherms of SO_2 adsorption. The isotherms of irreversible sorption are curves that have long initial linear sections (up to a filling degree of 47 % of the monolayer at 23 °C and up to 30 % at 200 °C)

and are typical of a surface that is uniform with respect to the heat of sorption.

The amounts of both reversible and irreversible sorption decrease as the temperature increases. In fact, at 23 °C, reversibly sorbed gas occupies 6.5 % of the monolayer (this evaluation is based on the geometric size of the molecule and the assumption that the surface has a continuous coating), while irreversibly sorbed gas covers 50.1 %. As the temperature increases to 200 °C, filling of the surface with the irreversibly sorbed gas decreases to 43.3 % of the monolayer, and filling with the reversibly adsorbed gas decreases to 5.6 %. Thus, the proportion of the reversible form is identical in both cases and is 11.5 % of the total amount of the gas sorbed.

The chemisorption of SO_2 , in contrast to that of Cl_2 , is not accompanied by variation of the relative electrical conductivity (σ/σ_0) . The σ/σ_0 value does not exceed 5.5 % over the whole temperature range studied, *i.e.*, SO_2 is predominantly chemisorbed on In_2O_3 in a weak uncharged form. Reversible and irreversible sorption are likely to occur on active sites of the same nature. In fact, according to the data of mass spectroscopic analysis, SO_2 is removed from the surface in the unchanged form; SO_2 sorbed at 23 °C is removed at 190 °C, and that sorbed at 200 °C is eliminated at 310 °C.

A comparison of the quantities of Cl_2 and SO_2 sorbed showed that under identical conditions (T and p_0) filling of the surface with SO_2 is twice as high as that with Cl_2 (Table 1). In the case of the consecutive sorption of Cl_2 and SO_2 , the situation changes dramatically. Preliminary chemisorption of Cl_2 results in a substantial (an order of magnitude) decrease in the amount of SO_2 sorbed. The results obtained make it possible to infer that the sorption of both Cl_2 and SO_2 occurs on sites of the same type. Since metal atoms⁵ are known to be the sites where the chemisorption of Cl_2 with charge transfer occurs, in the absence of Cl_2 , the molecules of SO_2 must also occupy the same sites.

Table 1. Chemisorption of Cl₂ and SO₂ on the surface of In₂O₃ (the initial pressure of the gas being sorbed was 0.5 Torr)

Gas	T/°C	Coefficients of Eq. (1)		Filling of the surface		The relative variation in the electrical
		$\frac{or Eq.}{a}$	<u>b</u>	μmol m ⁻²	% of the monolayer	conductivity, σ/σ_0
Cl ₂	23	0.064	0.363	0.66	10.0	0.444
	100	0.134	0.321	0.74	11.2	0.110
	150	0.158	0.327	0.93	14.1	0.086
	200	0.206	0.644	0.98	14.8	0.665
SO ₂	100	3.204	-3.992	1.44	21.2	0.980
	150	2.355	-2.892	1.17	17.7	1.050
	225	2.152	-4.422	0.94	14.2	1.010
SO ₂ after Cl ₂	100			0.09	1.4	1.270
	150	-	_	0.28	4.2	1.600
Cl ₂ after SO ₂	100	_		1.03	15.7	0.524
	150	_	_	0.79	12.0	0.008
	200	_	_	0.71	10.7	0.511

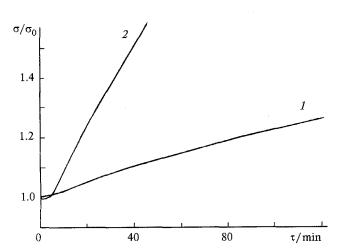


Fig. 2. The time variation of the relative electrical conductivity of In_2O_3 during chemisorption of SO_2 on a surface containing Cl_3 : 100 °C (1), 150 °C (2).

Although Cl_2 is sorbed in the dissociative form and each molecule occupies two adsorption sites, a molecule of SO_2 occupies only one active site.

At the same time, in contrast to sorption on the Cl₂-free surface, in the case of consecutive sorption, the amount of SO₂ chemisorbed increases with an increase in the temperature, which is typical of activated chemisorption. The character of the charge of the In₂O₃ surface also changes. In the presence of Cl₂, sorption of SO₂ is accompanied by a substantial increase in the conduction of In₂O₃ (Fig. 2); at 100 °C, 130 min after the beginning of the sorption, this increase is as high as 30 %. At higher temperatures, the increase in the conductance occurs more quickly.

It is known that SO₂ may be chemisorbed both in the donor and in acceptor forms, depending on the state of the oxide surface.^{6,7} In the presence of Cl₂, SO₂ is sorbed in the donor form, which may be due to variation in the coordination of the SO₂ molecules on the surface. In the presence of chlorine, SO₂ is probably sorbed on the acidic sites of the surface to give SO₃ complexes, which is supported by the data of mass spectral analysis of the desorption products.

The chemisorption of Cl_2 at 100 °C on a In_2O_3 surface containing sorbed SO_2 occurs at a higher rate than that without SO_2 , and the quantity of the Cl_2 sorbed is 40 % higher (see Table 1). No displacement of SO_2 from the surface to the gas phase is observed. When the temperature of sorption is increased to 150 and 200 °C, the amount of the consecutively sorbed Cl_2 decreases and becomes lower than that sorbed on a surface containing no SO_2 .

The preliminary sorption of SO_2 exerts an effect on the character of the variation of the conductance. The chemisorption of Cl_2 on In_2O_3 at $100\,^{\circ}C$ was accompanied by a monotonic decrease in the conductance, which

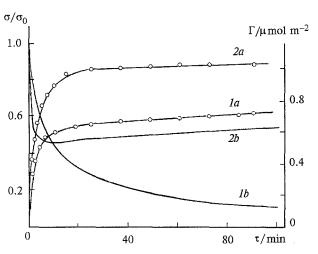


Fig. 3. The amount of gas sorbed (a) and the variation of the electrical conductivity (b) during chemisorption of Cl_2 on In_2O_3 at 100 °C: pure surface (1); surface containing SO_2 (2).

was the most pronounced in the initial period of sorption (up to three minutes), and the chlorine was desorbed unchanged.³ In the case when the oxide surface contained SO₂, the initial decrease in the conductance was considerably smaller than that without SO₂. At 100 °C, the rapid decrease in the conductance was followed by its slow growth (Fig. 3), which continued after the sorption of chlorine was completed.

In the chemisorption of Cl₂ at 150 and 200 °C, an increase in the conductance was also observed without the preliminary sorption of SO₂. It has been found previously³ that the increase in the conductance is caused by the formation of indium trichloride on the surface. In the case of the consecutive chemisorption of SO₂ and Cl₂ (100 °C), in addition to InCl₃, SO₃ and SO₂Cl₂ were also detected among the products of desorption.

An analysis of the results obtained showed that the regularities of the chemisorption of SO_2 on In_2O_3 are determined by the state of the surface layer of the oxide. In the absence of Cl_2 , the chemisorption of SO_2 on In_2O_3 is nonactivated and the surface does not become charged. Preliminary chemisorption of Cl_2 , which causes a decrease in the concentration of free electrons in the surface layer of the oxide, results in a change in the form of the SO_2 sorbed, as indicated by the increase in the conductance of the oxide.

When the order of the sorption is changed (Cl₂ after SO₂), chemisorption is complicated by the formation of the products of chlorination, which are formed at lower temperatures in the presence of SO₂ than in the absence of SO₂. One may suggest that redistribution of the electron density in the surface layer of the oxide, which accompanies binding of the surface oxygen to SO₃ groups, facilitates the chemisorption of chlorine, cleavage of the indium—oxygen bond, and the formation of the chloride. However, the possibility of chlorination of the

surface by SO₂Cl₂, which was observed by mass spectrometry, cannot be ruled out.

In the absence of SO_2 , the formation of chlorination products was noted only above 150 °C. With the preliminary sorption of SO_2 , the concentration of these products on the surface increases. The fact that the oxide surface is occupied by the reaction products probably leads to a decrease in the amount of chlorine sorbed at 150-200 °C.

Thus, the studies of the chemisorption of Cl_2 and SO_2 on In_2O_3 and of the change in the electrical conductivity of the oxide have shown that the character of the interference of these gases depends on the order in which they are sorbed. Modification of the oxide surface prior to the chemisorption of a gas results in a change in the reactivity of the solid. Chlorides formed at lower temperatures during the chemisorption of Cl_2 on a surface with SO_2 than on SO_2 -free surface. The preliminary chemisorption of Cl_2 , in turn, caused changes in the charge of the surface during the subsequent adsorption of SO_2 .

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